20 V single N-channel Trench MOSFET 6 July 2012

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Trench MOSFET technology
- Very fast switching
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection

1.3 Applications

- Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portables
- Hard disk and computing power management

1.4 Quick reference data

Table 1. Qui	ick reference data						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	-	11.3	А
Static charact	teristics	·					
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 7.9 A; T _j = 25 °C		-	14	18	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².





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2. Pinning information

Table 2.	Pinning	information			
Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	D	drain		D	
2	D	drain			
3	G	gate		G	
4	S	source		\$ 017aaa253	
5	D	drain	Transparent top view DFN2020MD-6 (SOT1220)	Transparent top view	077442200
6	D	drain			
7	D	drain			
8	S	source			

3. Ordering information

Table 3. Ordering information							
Type number	Package	Package					
	Name	Description	Version				
PMPB12UN	DFN2020MD-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220				

4. Marking

Table 4. Marking codes	
Type number	Marking code
PMPB12UN	1F

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	11.3	А
		V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	7.9	А
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	5	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	31	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1]	-	1.7	W
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Symbol	Parameter	Conditions		Min	Max	Unit
		T _{amb} = 25 °C; t ≤ 5 s	[1]	-	3.5	W
		T _{sp} = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	in diode				1	,
I _S	source current	T _{amb} = 25 °C	[1]	-	1.8	А

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

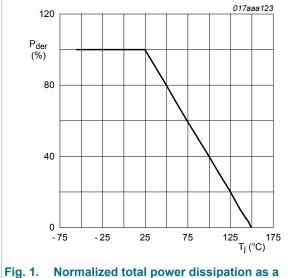


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

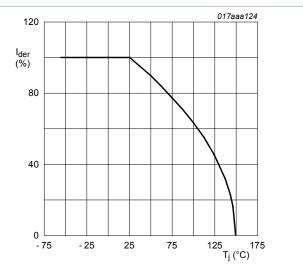
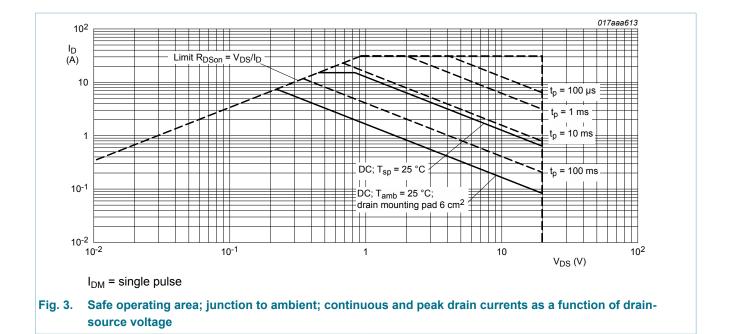


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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6. Thermal characteristics

Table 6. Th	nermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R _{th(j-a)}	thermal resistance	in free air	[1]	-	235	270	K/W
	from junction to ambient		[2]	-	67	74	K/W
	ampient		[3]	-	33	36	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	5	10	K/W

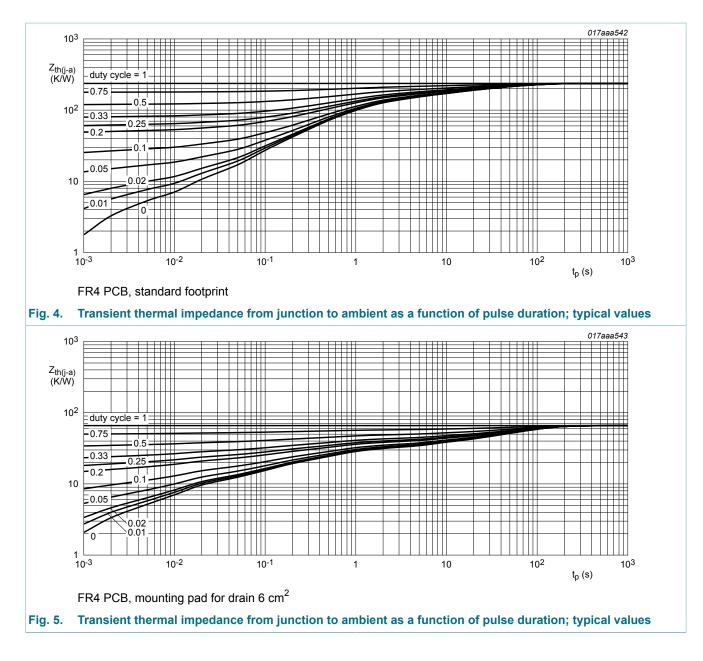
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm², t \leq 5 s

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7. Characteristics

Table 7. Ch	naracteristics							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit	
Static characteristics								
V _{(BR)DSS}	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		20	-	-	V	
V _{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} = V _{GS} ; T _j = 25 °C		0.4	0.7	1	V	
I _{DSS}	drain leakage current	V_{DS} = 20 V; V_{GS} = 0 V; T_j = 25 °C		-	-	1	μA	
		V_{DS} = 20 V; V_{GS} = 0 V; T_j = 150 °C		-	-	100	μA	
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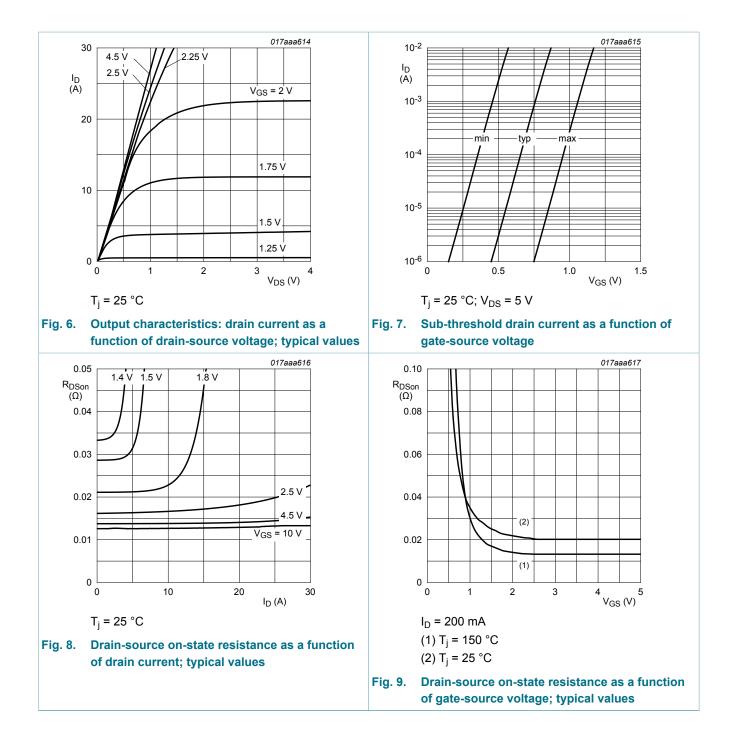
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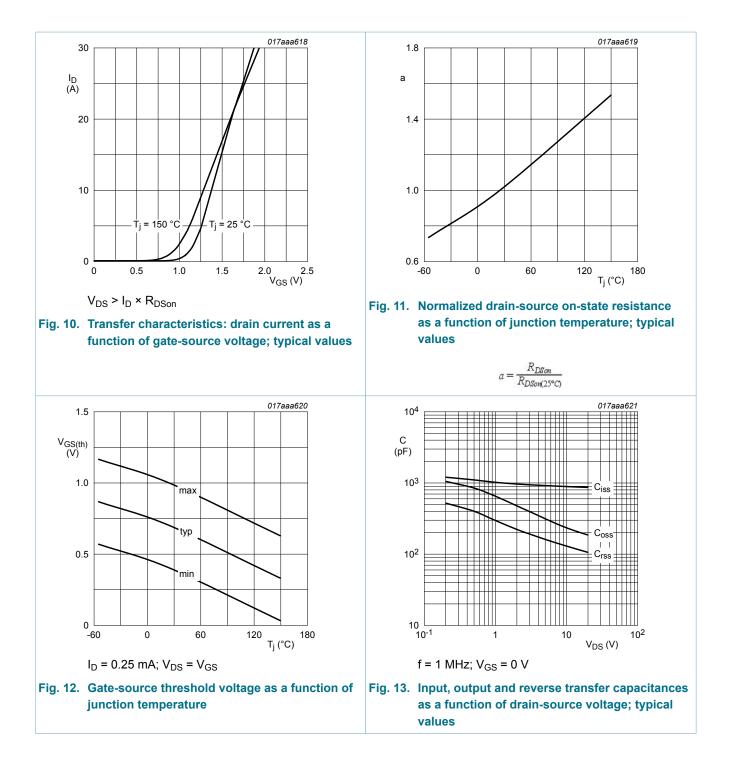
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GSS}	gate leakage current	V_{GS} = 8 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -8 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	V_{GS} = 4.5 V; I _D = 7.9 A; T _j = 25 °C	-	14	18	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 7.9 A; T _j = 150 °C	-	21	27	mΩ
		V_{GS} = 2.5 V; I _D = 3.5 A; T _j = 25 °C	-	17	23	mΩ
		V _{GS} = 1.8 V; I _D = 3.5 A; T _j = 25 °C	-	21	33	mΩ
9fs	forward transconductance	V _{DS} = 10 V; I _D = 7.9 A; T _j = 25 °C	-	25	-	S
R _G	gate resistance	f = 1 MHz	-	1.4	-	Ω
Dynamic cl	haracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = 10 V; I _D = 6 A; V _{GS} = 4.5 V; T _j = 25 °C	-	8.8	13	nC
Q _{GS}	gate-source charge		-	1	-	nC
Q _{GD}	gate-drain charge		-	2.2	-	nC
C _{iss}	input capacitance	V_{DS} = 10 V; f = 1 MHz; V_{GS} = 0 V;	-	886	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	233	-	pF
C _{rss}	reverse transfer capacitance		-	129	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 10 V; I _D = 6 A; V _{GS} = 4.5 V;	-	9	-	ns
t _r	rise time	R _{G(ext)} = 6 Ω; T _j = 25 °C	-	20	-	ns
t _{d(off)}	turn-off delay time		-	26	-	ns
t _f	fall time		-	26	-	ns
Source-dra	in diode	, , , , , , , , , , , , , , , , , , , ,	1			
V _{SD}	source-drain voltage	I _S = 1.8 A; V _{GS} = 0 V; T _j = 25 °C	-	0.6	1.2	V

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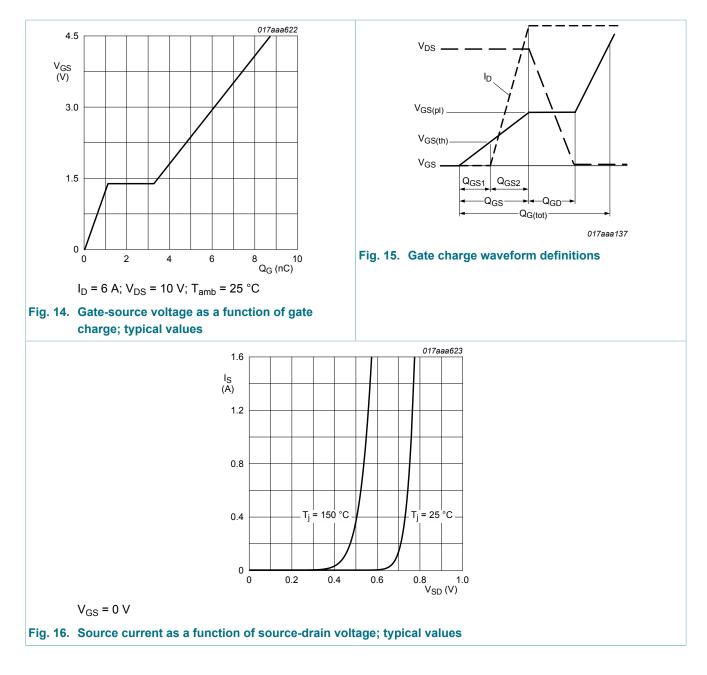


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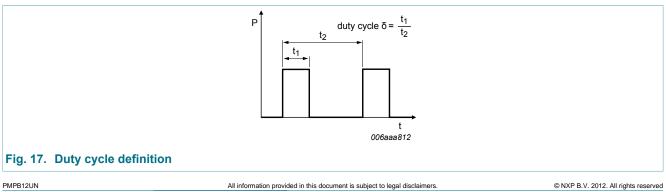


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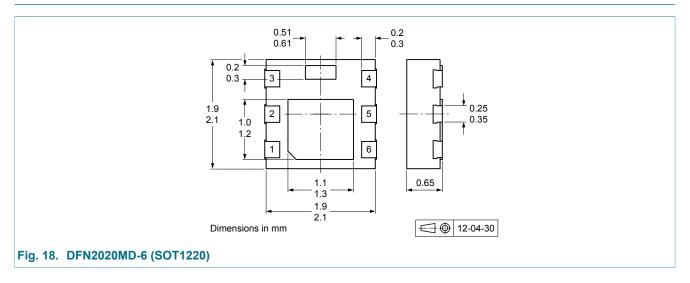


Test information 8.



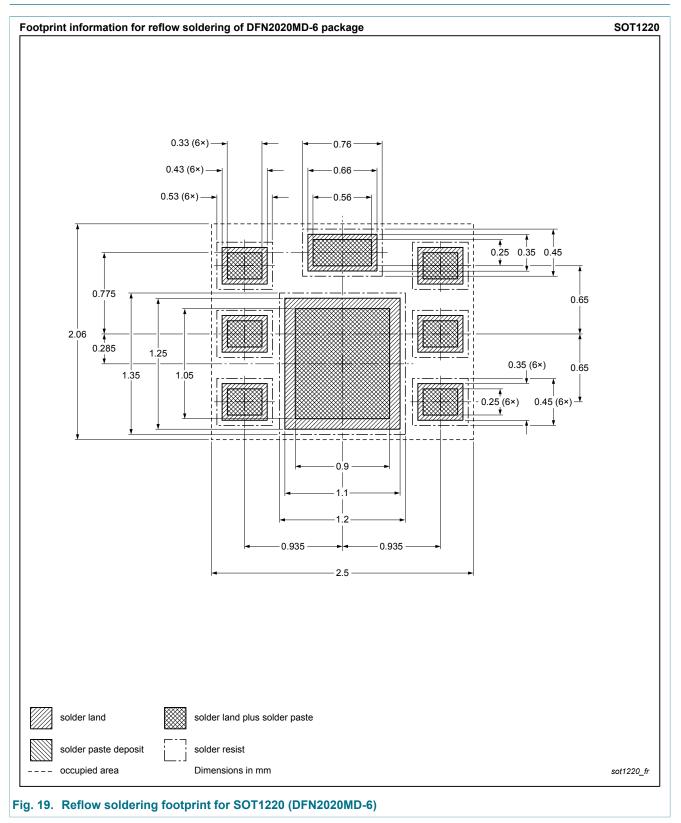
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9. Package outline



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10. Soldering



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11. Revision history

Table 8. Revision history								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PMPB12UN v.1	20120706	Product data sheet	-	-				

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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